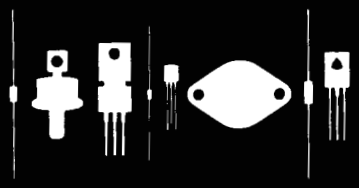
Central
Semiconductor Corp.
145 Adams Avenue
Hauppauge, New York 11788



2N5758 2N5759 2N5760 NPN
2N6226 2N6227 2N6228 PNP

COMPLEMENTARY SILICON POWER TRANSISTORS

JEDEC TO-3 CASE

DESCRIPTION

The CENTRAL SEMICONDUCTOR 2N5758, 2N6226 series types are complementary silicon power transistors manufactured by the epitaxial base process mounted in a hermetically sealed metal case designed for medium power amplifier and switching applications where high voltages are required.

MAXIMUM RATINGS (T_C=25°C unless otherwise noted)

	SYMBOL	2N5758 2N6226	2N5759 2N6227	2N5760 2N6228	UNIT
Collector-Base Voltage	V_{CBO}	100	120	140	V
Collector-Emitter Voltage	V_{CEO}	100	120	140	V
Emitter-Base Voltage	V_{EBO}	7.0	7.0	7.0	V
Collector Current	I_C	6.0	6.0	6.0	A
Collector Current (PEAK)	I_{CM}	10	10	10	A
Base Current	I_B	4.0	4.0	4.0	A
Power Dissipation	P_D	150	150	150	W
Operating and Storage Junction Temperature	T_J, T_{STG}		-65 TO +200		°C
Thermal Resistance	Θ_{JC}		1.17		°C/W

ELECTRICAL CHARACTERISTICS (T_C=25°C unless otherwise noted)

		2N5758 2N6226		2N5759 2N6227		2N5760 2N6228		
SYMBOL	TEST CONDITIONS	MIN	MAX	MIN	MAX	MIN	MAX	UNIT
I_{CBO}	V_{CB}=Rated V_{CBO}		1.0		1.0		1.0	mA
I_{CEV}	V_{CE}=Rated V_{CBO}, $V_{BE(OFF)}$=1.5V		1.0		1.0		1.0	mA
I_{CEV}	V_{CE}=Rated V_{CBO}, $V_{BE(OFF)}$=1.5V, T_C=150°C		5.0		5.0		5.0	mA
I_{CEO}	V_{CE}=½ Rated V_{CEO}		1.0		1.0		1.0	mA
I_{EBO}	V_{BE}=7.0V		1.0		1.0		1.0	mA
BV_{CEO}	I_C=200mA	100		120		140		V
$V_{CE(SAT)}$	I_C=3.0A, I_B=0.3A		1.0		1.0		1.0	V
$V_{CE(SAT)}$	I_C=6.0A, I_B=1.2A		2.0		2.0		2.0	V
$V_{BE(ON)}$	V_{CE}=2.0V, I_C=3.0A		1.5		1.5		1.5	V
h_{FE}	V_{CE}=2.0V, I_C=3.0A	25	100	20	80	15	60	
h_{FE}	V_{CE}=2.0V, I_C=6.0A	5.0		5.0		5.0		
h_{fe}	V_{CE}=10V, I_C=2.0A, f=1.0kHz	15		15		15		
f_T	V_{CE}=20V, I_C=0.5A, f=0.5MHz	1.0		1.0		1.0		MHz
C_{ob}	V_{CB}=10V, I_E=0, f=0.1MHz		300		300		300	pF

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